

Docket No.: 050099-0246



PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of : Customer Number: 20277  
Tatsuya KUNIKIYO, et al. : Confirmation Number: CNF NO. 4732  
Application No.: 10/797,199 : Group Art Unit: 2824  
Filed: March 11, 2004 : Examiner: A. Q. Tran

For: MAGNETIC MEMORY DEVICE CAPABLE OF PASSING BIDIRECTIONAL  
CURRENTS THROUGH THE BIT LINES (As Amended)

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

This Information Disclosure Statement is being filed more than three months after the U.S. filing date and after the mailing date of a Final Rejection or Notice of Allowance, but before payment of the Issue Fee.

**REQUEST TO CONSIDER REFERENCES AFTER CLOSE OF PROSECUTION AND  
BEFORE PAYMENT OF ISSUE FEE**

The undersigned hereby requests consideration and entry of this Information Disclosure Statement and accompanying references under 37 CFR 1.97(d).

Please charge the processing fee under 1.17(p) of \$180.00 to Deposit Account 500417.

06/15/2005 SDENB0B1 00000030 500417 10797199

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**CERTIFICATION PARAGRAPH**

The undersigned certifies that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a

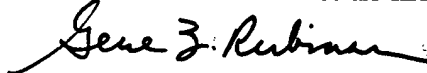
counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement as described in 37 CFR 1.97(e)(1).

Each non-English language reference was cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the foreign search report or office action, together with an English language version thereof, is attached for the Examiner's information.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Date: June 13, 2005**

**Please recognize our Customer No. 20277  
as our correspondence address.**



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. <b>050099-0246</b>		SERIAL NO. <b>10/797,199</b>	
				APPLICANT <b>Tatsuya KUNIKIYO, et al.</b>			
				FILING DATE <b>March 11, 2004</b>		GROUP <b>2824</b>	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 5,793,697	8-11-1998	Scheuerlein			
		US 5,852,574	12-22-1998	Naji			
		US					
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		US					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		EP 1 094 467 A2	4-25-2001	MOTOROLA, INC		X	
		JP 63-044398	2-25-1988				X
		JP 05-095055	4-16-1993				X
		JP 11-289186	10-19-1999				X
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		SCHEUERLEIN, R.E.: "Magnetoresistive IC memory Limitations and Architecture Implications, IEEE Nonvolatile Memory Technology Conference, June 22-24, 1998, 47-50					
		ITO, K. et al.: "Reviews and Prospects of High-Density RAM Technology" International Semiconductor Conference Proceedings, Vol. 1, October 10-14, 2000, 13-22					
		SCHEUERLEIN, R. et al.: "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", IEEE International Solid-State Circuits Conference, February 7-9, 2000, 128-129					
		DURLAM, M. et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", IEEE International Solid-State Circuits Conference, February 7-9, 2000, 130-131					
		JOHNSON, M.: "Magnetoelectronic memories last and last", IEEE Spectrum Vol. 37 No. 2 February 2000, 33-40					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.